Ultra low capacitance bidirectional ESD protection diodes

Rev. 01 — 30 October 2008

**Product data sheet** 

#### **Product profile** 1.

### 1.1 General description

Ultra low capacitance bidirectional ElectroStatic Discharge (ESD) protection diodes in small Surface-Mounted Device (SMD) plastic packages designed to protect one signal line from the damage caused by ESD and other transients.

The devices may also be used for unidirectional ESD protection of up to two signal lines.

**Product overview** Table 1.

Type number	Package		Package configuration				
	NXP	JEDEC					
PESD5V0X1BQ	SOT663	-	ultra small and flat lead				
PESD5V0X1BT	SOT23	TO-236AB	very small				

#### 1.2 Features

- Bidirectional ESD protection of one line ESD protection up to 9 kV
- Unidirectional ESD protection of up to IEC 61000-4-2; level 4 (ESD) two lines
- Ultra low diode capacitance: C<sub>d</sub> = 0.9 pF AEC-Q101 qualified
- Very low leakage current: I<sub>RM</sub> = 1 nA

### 1.3 Applications

- USB interfaces
- Antenna protection
- Radio Frequency (RF) protection
- 10/100/1000 Mbit/s Ethernet
- FireWire
- Asymmetric Digital Subscriber Line (ADSL)
- High-speed data lines

- Subscriber Identity Module (SIM) card protection
- Computers, peripherals and printers
- Cellular handsets and accessories
- Portable electronics
- Communication systems
- Audio and video equipment



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#### 1.4 Quick reference data

Table 2. Quick reference data

 $T_{amb}$  = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diode						
$V_{RWM}$	reverse standoff voltage		-	-	5	V
$C_{d}$	diode capacitance	$f = 1 MHz; V_R = 0 V$	[1]	0.9	1.3	pF
			[2] _	2	2.6	pF

<sup>[1]</sup> Bidirectional configuration: measured from pin 1 to 2 or pin 2 to 1.

# 2. Pinning information

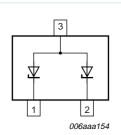
Table 3. Pinning

Table 3.	Filling		
Pin	Description	Simplified outline	Graphic symbol
PESD5V0	X1BQ		
1	cathode (diode 1)		
2	cathode (diode 2)	3	3
3	common anode	1 2	
			006aaa154



1	cathode (diode 1)
2	cathode (diode 2)
3	common anode





# 3. Ordering information

Table 4. Ordering information

Type number	Package				
	Name	Description	Version		
PESD5V0X1BQ	<b>'-</b>	plastic surface-mounted package; 3 leads	SOT663		
PESD5V0X1BT	-	plastic surface-mounted package; 3 leads	SOT23		

<sup>[2]</sup> Unidirectional configuration: measured from pin 1 to 3 or pin 2 to 3.

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# 4. Marking

Table 5. Marking codes

Type number	Marking code <sup>[1]</sup>
PESD5V0X1BQ	E6
PESD5V0X1BT	U3*

<sup>[1] \* = -:</sup> made in Hong Kong

# 5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per device					
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-55	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

Table 7. ESD maximum ratings

T<sub>amb</sub> = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Max	Unit
Per diode						
V <sub>ESD</sub>	electrostatic discharge voltage IEC 61000-4-2 (contact discharge)		<u>[1]</u>	-	9	kV
		MIL-STD-883 (human body model)		-	10	kV

<sup>[1]</sup> Device stressed with ten non-repetitive ESD pulses.

Table 8. ESD standards compliance

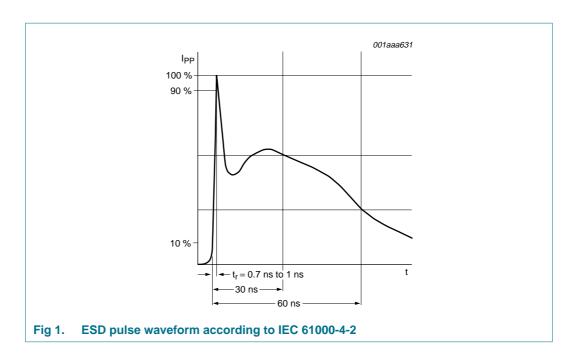
Standard	Conditions
Per diode	
IEC 61000-4-2; level 4 (ESD)	> 8 kV (contact)
MIL-STD-883; class 3 (human body model)	> 4 kV

<sup>\* =</sup> p: made in Hong Kong

<sup>\* =</sup> t: made in Malaysia

<sup>\* =</sup> W: made in China

### Ultra low capacitance bidirectional ESD protection diodes



## 6. Characteristics

Table 9. Characteristics

 $T_{amb}$  = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per diod	е						
$V_{\text{RWM}}$	reverse standoff voltage			-	-	5	V
$I_{RM}$	reverse leakage current	$V_{RWM} = 5 V$		-	1	100	nA
$V_{BR}$	breakdown voltage	$I_R = 5 \text{ mA}$		5.8	7.5	9.5	V
C <sub>d</sub>	diode capacitance	f = 1 MHz					
	V <sub>R</sub> = 0 V	[1]	-	0.9	1.3	pF	
			[2]	-	2	2.6	pF
		$V_R = 5 V$	[1]	-	8.0	1.2	pF
			[2]	-	1.7	2.3	pF
r <sub>dif</sub>	differential resistance	$I_R = 1 \text{ mA}$		-	-	100	Ω

<sup>[1]</sup> Bidirectional configuration: measured from pin 1 to 2 or pin 2 to 1.

<sup>[2]</sup> Unidirectional configuration: measured from pin 1 to 3 or pin 2 to 3.

### Ultra low capacitance bidirectional ESD protection diodes

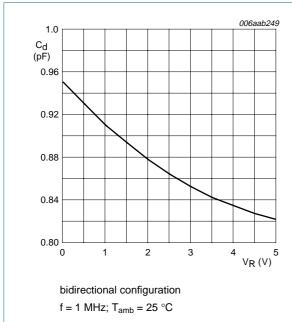
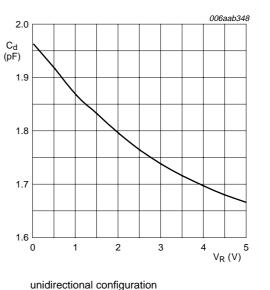


Fig 2. Diode capacitance as a function of reverse voltage; typical values



 $f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$ 

Fig 3. Diode capacitance as a function of reverse voltage; typical values

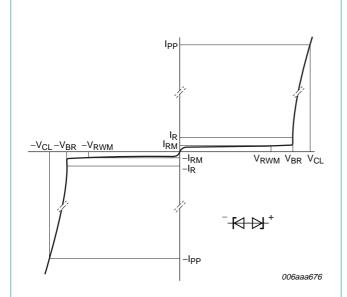


Fig 4. V-I characteristics for a bidirectional **ESD** protection diode

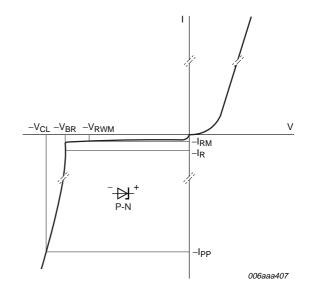
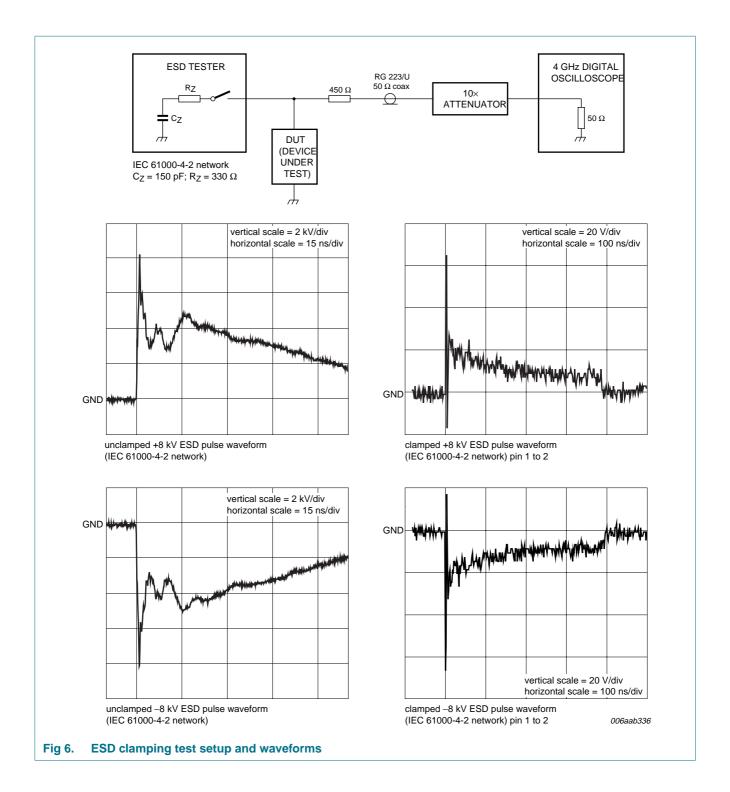


Fig 5. V-I characteristics for a unidirectional **ESD** protection diode

#### Ultra low capacitance bidirectional ESD protection diodes



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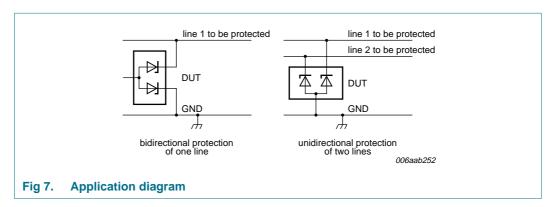
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## 7. Application information

PESD5V0X1BQ and PESD5V0X1BT are designed for the protection of one bidirectional data or signal line from the damage caused by ESD. The devices may be used on lines where the signal polarities are both, positive and negative with respect to ground.

PESD5V0X1BQ and PESD5V0X1BT may also be used for the protection of two unidirectional data or signal lines, which have positive signal polarities with respect to ground.



#### Circuit board layout and protection device placement

Circuit board layout is critical for the suppression of ESD and Electrical Fast Transient (EFT). The following guidelines are recommended:

- 1. Place the device as close to the input terminal or connector as possible.
- 2. The path length between the device and the protected line should be minimized.
- 3. Keep parallel signal paths to a minimum.
- 4. Avoid running protected conductors in parallel with unprotected conductors.
- 5. Minimize all Printed-Circuit Board (PCB) conductive loops including power and ground loops.
- 6. Minimize the length of the transient return path to ground.
- 7. Avoid using shared transient return paths to a common ground point.
- 8. Ground planes should be used whenever possible. For multilayer PCBs, use ground vias.

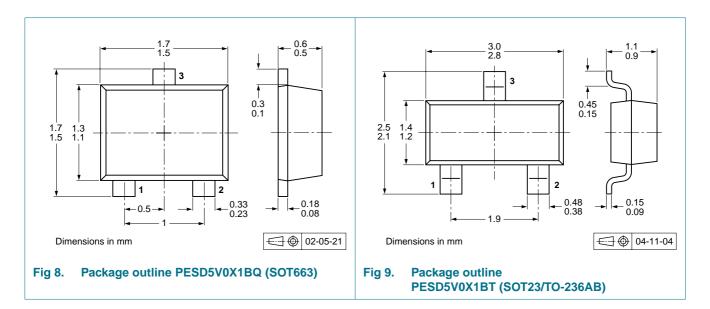
#### 8. Test information

### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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# 9. Package outline



# 10. Packing information

Table 10. Packing methods

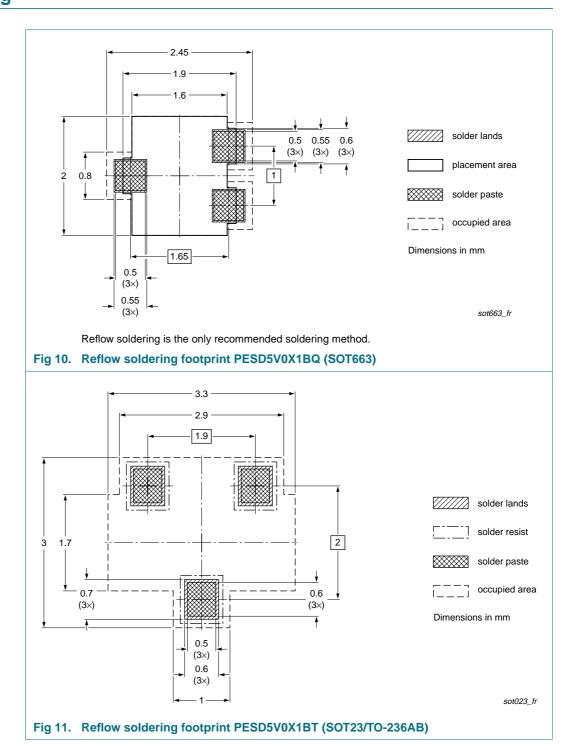
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing	quantity		
			3000	4000	8000	10000
PESD5V0X1BQ	SOT663	2 mm pitch, 8 mm tape and reel	-	-	-315	-
		4 mm pitch, 8 mm tape and reel	-	-115	-	-
PESD5V0X1BT	SOT23	4 mm pitch, 8 mm tape and reel	-215	-	-	-235

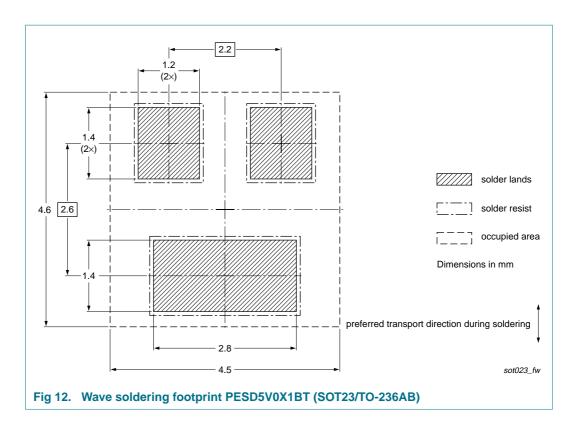
[1] For further information and the availability of packing methods, see  $\underline{\text{Section 14}}$ .

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# 11. Soldering



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# 12. Revision history

### Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PESD5V0X1BQ_PESD5V0X1BT_1	20081030	Product data sheet	-	-

#### Ultra low capacitance bidirectional ESD protection diodes

## 13. Legal information

#### 13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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### **NXP Semiconductors**

# PESD5V0X1BQ; PESD5V0X1BT

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Date of release: 30 October 2008

Document identifier: PESD5V0X1BQ\_PESD5V0X1BT\_1